

Notice of References Cited			Application/Control No.	Applicant(s)/Patent Under Reexamination	
			10/580,625	HUETING ET AL.	
			Examiner	Art Unit	Page 1 of 1
			Hsin-Yi (Steven) Hsieh	2811	

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2001/0003367 A1	06-2001	HSHIEH et al.	257/330
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	JP 03211885 A	09-1991	Japan	MIYANO et al.	H01L 29/784
	O	EP 1168455 A2	01-2002	European Patent	OMURA et al.	H01L 29/78
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Onda et al., "SiC Integrated MOSFETs" Physica Status Solidi (A), Applied Research, Berlin, DE, vol. 162, no. 1, 16 July 1997, pages 369-388
	V	
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.